

E³S Annual Retreat, September 7-8, 2017, MIT

Welcome and Review of Agenda

Eli Yablonovitch

Director

Center for Energy Efficient Electronics Science



A Science & Technology Center

Berkeley
UNIVERSITY OF CALIFORNIA

**Massachusetts
Institute of
Technology**

STANFORD
UNIVERSITY

THE UNIVERSITY OF
TEXAS AT EL PASO

FLORIDA
INTERNATIONAL
UNIVERSITY

CALIFORNIA COMMUNITY COLLEGES
CHANCELLOR'S OFFICE



Center for Energy Efficient
Electronics Science

This is a Private Meeting.

This is not a public disclosure of information.

For our corporate partners, please share the information from this meeting with your Company to help build bridges between your Company and the Center.



Welcome to the 2017 E³S Annual Retreat

- **E³S Faculty, Students, Postdocs and Staff**
 - Berkeley
 - MIT
 - Stanford
 - UTEP
 - FIU
- **Industry Partners**
 - **IBM:** Paul Solomon



Retreat Agenda: Day 1, Thursday, September 7

Time	Activity / Topic	Speakers
7:30 AM	<i>Breakfast & Check-In</i>	
8:00 AM	Welcome & Introduction	
	Review of Agenda	
	Goals for the Retreat	Eli Yablonovitch
	Center Overview	
8:30 AM	Theme I: Nanoelectronics	
	Theme I Overview	Eli Yablonovitch
	Progress on III-V Nanowire Transistor Project	Jesús del Alamo
	Progress on 2D Chalcogenide Transistor Project	Ali Javey
	Progress on Graphene Nanoribbon Project	Eli Yablonovitch
	Open Discussion	
9:45 AM	<i>Break</i>	



Retreat Agenda: Day 1 *continued*

10:00 AM

Theme II: Nanomechanics

Theme II Overview

Tsu-Jae King Liu

Progress on NEM Relay Project

Bivas Saha

Progress on Squitch Project

Farnaz Niroui

Progress on Stritch Project

David Zubia

Open Discussion

11:15 AM

Keynote Presentation

Large-Scale Photonic Integrated Circuits for Quantum Information Science and Machine Learning

Dirk Englund

12:00 PM

Lunch

1:00 PM

Theme III: Nanophotonics

Theme III Overview

Ming Wu

Progress on III-V Epitaxial Growth

Eugene Fitzgerald

Progress on Antenna-Enhanced LEDs

Seth Fortuna

Open Discussion



Retreat Agenda: Day 1 *continued*

2:25 PM	Theme IV: Nanomagnetism	
	Theme IV Overview and Ultrafast Magnetic Switching	Jeffrey Bokor
	Spin-Orbit Torque Switching Project	Charles-Henri Lambert
	CMOS Integration Project	Jean-Anne Incorvia
	Open Discussion	
3:40 PM	Knowledge Transfer	Michael Bartl
3:50 PM	<i>Break</i>	
4:00 PM	Meeting with Industry Partners	
4:45 PM	<i>Walk to Poster Session & Dinner</i>	
5:15 PM	Reception and Poster Session	
	Café ArtScience, 650 East Kendall St., Cambridge (www.cafeartscience.com)	
6:30 PM	Dinner and Recognitions	
	Café ArtScience, 650 East Kendall St., Cambridge	



Retreat Agenda: Day 2, Friday, September 8

Time	Activity / Topic	Speaker / Facilitator
7:30 AM	<i>Breakfast</i>	
8:00 AM	System Integration System Integration Overview Open Discussion	Vladimir Stojanović
8:30 AM	Elevator Pitches 90-Seconds Research Presentations Feedback & Discussion	E³S Students & Postdocs Moderators: Lea Marlor, Kedrick Perry
10:00 AM	<i>Break</i>	



Retreat Agenda: Day 2, *continued*

10:15 AM

Education and Diversity

Inclusion and Diversity Overview

Kedrick Perry

Education Overview

Lea Marlor

Open Discussion

11:15 AM

Center Management

Michael Bartl

11:30 AM

A Look Beyond 2020: Center Legacy

Open Discussion

Moderator:

Vladimir Bulović

11:55 AM

Closing Remarks

Eli Yablonovitch

12:00 PM

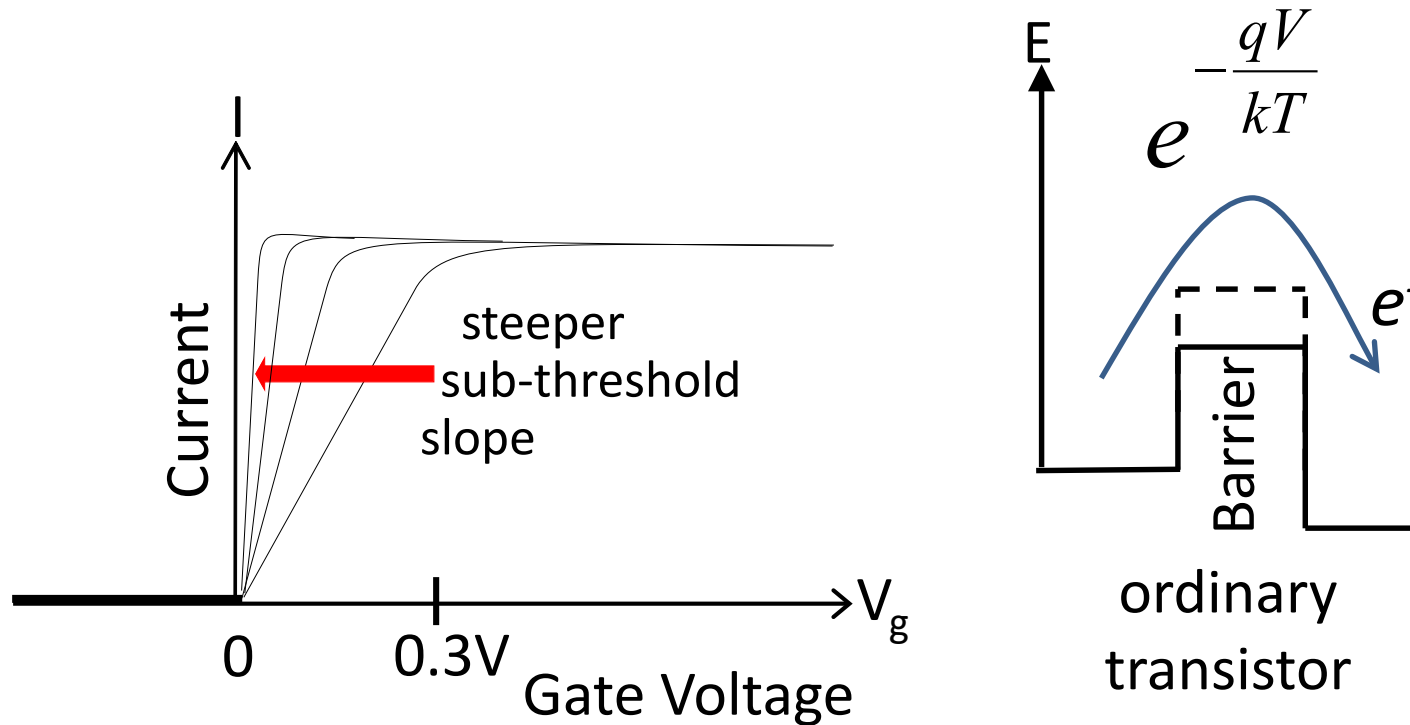
Lunch (boxed)



Vision for 2025: Swarms of Electronics



The Next Transistor: A New More Sensitive Electronic Switch



Take the powering voltage from ~ 1 Volt down to milli-Volts
(noise is in μ Volts)



The New Switch has to Satisfy Three Specifications

1. Steepness (or sensitivity)

switches with only a few milli-volts
60mV/decade \Rightarrow **1mV/decade**

2. On/Off ratio. **$10^6 : 1$**

3. Current Density or Conductance Density (for miniaturization)

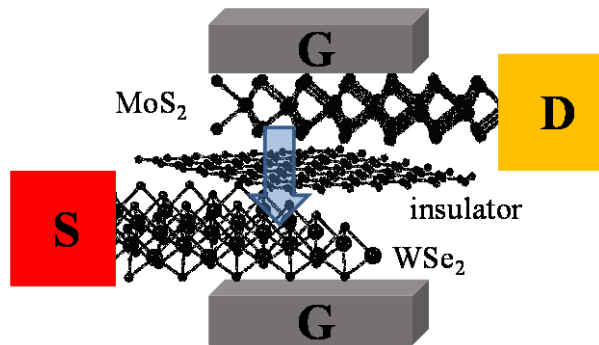
old spec at 1Volt: 1 mAmp/micron

our spec: **1 milli-Siemen/micron**

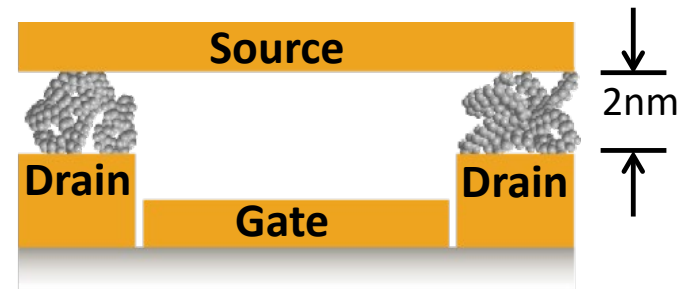
A One micron device should conduct at $1k\Omega$ in the on-state.



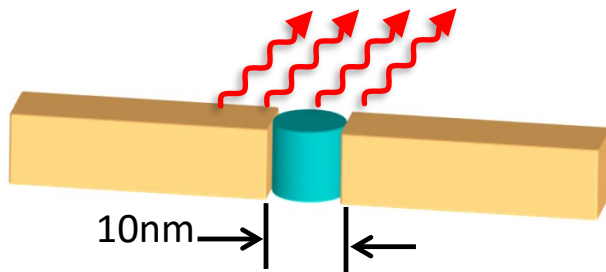
Four Interconnected Approaches



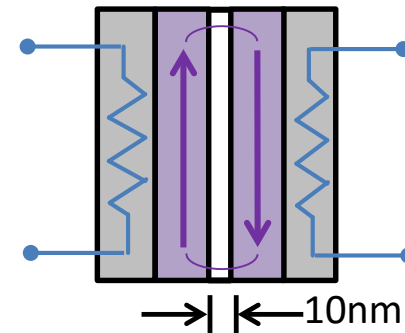
Nanoelectronics:
Solid-State Milli-Volt Switching



Nanomechanics:
Zero-Leakage Switching

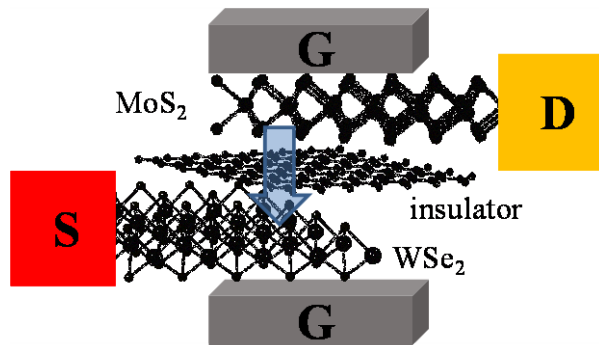


Nanophotonics:
Ultra-Low Energy Communication



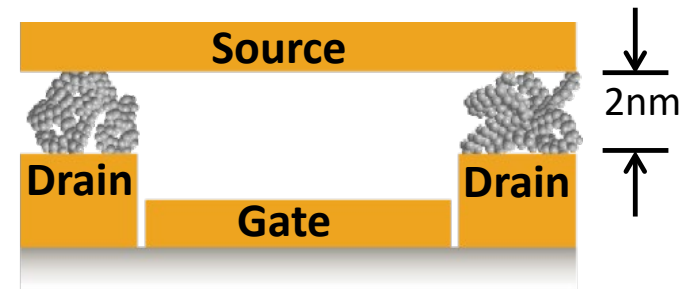
Nanomagnetics:
A Low Energy Magnetic Switch

Each Theme has an Issue--maybe embarrassing— That we can discuss freely at this Retreat.



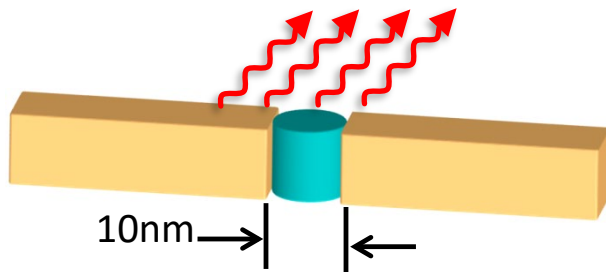
Nanoelectronics:

Solid-State Milli-Volt Switching



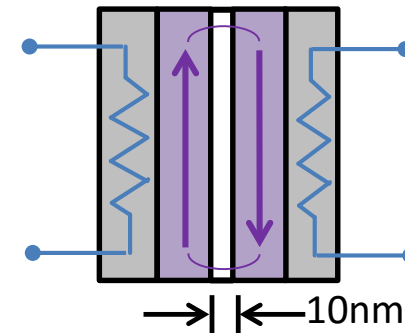
Nanomechanics:

Zero-Leakage Switching



Nanophotonics:

Ultra-Low Energy Communication



Nanomagnetics:

A Low Energy Magnetic Switch



STEEP TRANSISTORS WORKSHOP 2016

ESSDERC/EPFL, Lausanne, Switzerland
September 11 - 12, 2016

Following the first successful workshop at University of Notre Dame, USA, a second workshop related to Steep Slope Transistors will be arranged in combination with the ESSDERC conference at EPFL, Lausanne, Switzerland. Steep transistors with subthreshold swings less than 60 mV/decade are attracting attention worldwide due to their promise to enable electronic systems operating at 300 mV and below. Interband tunneling or internal gain mechanisms in the gate enable the



Organizing committee:

Lars-Erik Wernersson

Alan Seabaugh

Kirsten Moselund

Aaron Thean

Eli Yablonovitch

Adrian Ionescu

Lund University, Sweden (Chair)

University of Notre Dame, USA

IBM Zuerich, Switzerland

IMEC, Belgium

University of California Berkeley, USA Adrian

EPFL, Switzerland

The 2017 Symposium &
Workshop will be held at
Berkeley;
Oct. 19-20, 2017



Berkeley Symposium on Energy Efficient Electronics

Fifth Berkeley Symposium on Energy Efficient
Electronic Systems and Steep Transistors Workshop

October 19-20, 2017

Sutardja Dai Hall, University of California, Berkeley, California, USA



Keynote Speaker:

Amir Khosrowshani, Intel Corporation, USA

Topic: Analog and digital accelerators for deep learning

Invited Speakers:

Jeffrey Bokor, University of California, Berkeley, USA

Topic: Ultra-high-speed magnetic switching

Gert Cauwenberghs, University of California, San Diego, USA

Topic: Energy efficiency of adaptive neural circuits

Jesus del Alamo, Massachusetts Institute of Technology, USA

Topic: I-V spectroscopy of the electronic energy levels in nanopillars

Paolo Gargini, ITRS, USA

Topic: Roadmap evolution: from NTRS to ITRS, from ITRS 2.0 to IRDS

Takahiro Hanyu, Tohoku University, Japan

Topic: Potential energy savings through the integration of logic and memory

Ru Huang, Peking University, China

Topic: Tunneling switches: characteristics and improving performance

Adrian Ionescu, Ecole Polytechnique Fédérale Lausanne, Switzerland

Topic: Sub-unity body factor: the next CMOS and beyond CMOS technology booster



Engin Ipek, University of Rochester, USA

Topic: Analog accelerators, as part of a digital systems

Masaharu Kobayashi, University of Tokyo, Japan

Topic: Negative Capacitance as a pathway toward lower voltage transistors

Zoran Krivokapic, GlobalFoundries, USA

Topic: Negative Capacitance Transistors

Subhasish Mitra, Stanford University, USA

Topic: Systems benefits and the technology of 3D integration

Oleg Mukhanov, Hypres, USA

Topic: Rapid single flux quantum technology

Hideo Ohno, Tohoku University, Japan

Topic: Use of magnetism in performing neuro-morphic computing functions

Lucian Prejbeanu, SPINTEC, CEA Grenoble, France

Topic: High-speed magnetic switching

Sayeef Salahuddin, University of California, Berkeley, USA

Topic: Metastable ferro-electric gate insulators for reducing the operating voltage of transistors



Alan Seabaugh, University of Notre Dame, USA

Topic: Optimizing TFET switching characteristics

Marin Soljacic, Massachusetts Institute of Technology, USA

Topic: Analog optical processing to assist deep learning

Shinichi Takagi, University of Tokyo, Japan

Topic: Improving the characteristics of tunnel switches

Anne Verhulst, IMEC, Leuven, Belgium

Topic: Conduction and valence band wavefunction mismatch in limiting tunneling currents

Lars-Erik Wernersson, Lund University, Sweden

Topic: Nanowire I-V spectroscopy to measure steepness of semiconductor bandedges

Masanao Yamaoka, Hitachi, Japan

Topic: Suitability of spin-Ising chips to solve combinatorial optimization problems

Education & Diversity Goals

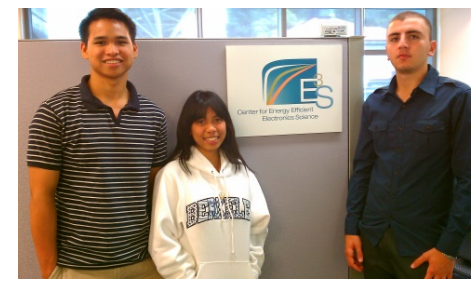
- Professional Development
(including Leadership Certificate for graduate students and postdocs)
- Community Colleges
(Transfer to Excellence Program and Research Experience for Teachers)
- Broadening Participation
(REU, HBCU-REU, workshops, outreach to schools and communities)





Transfer-to-Excellence Program

Created a National Model of Student Transfer Success



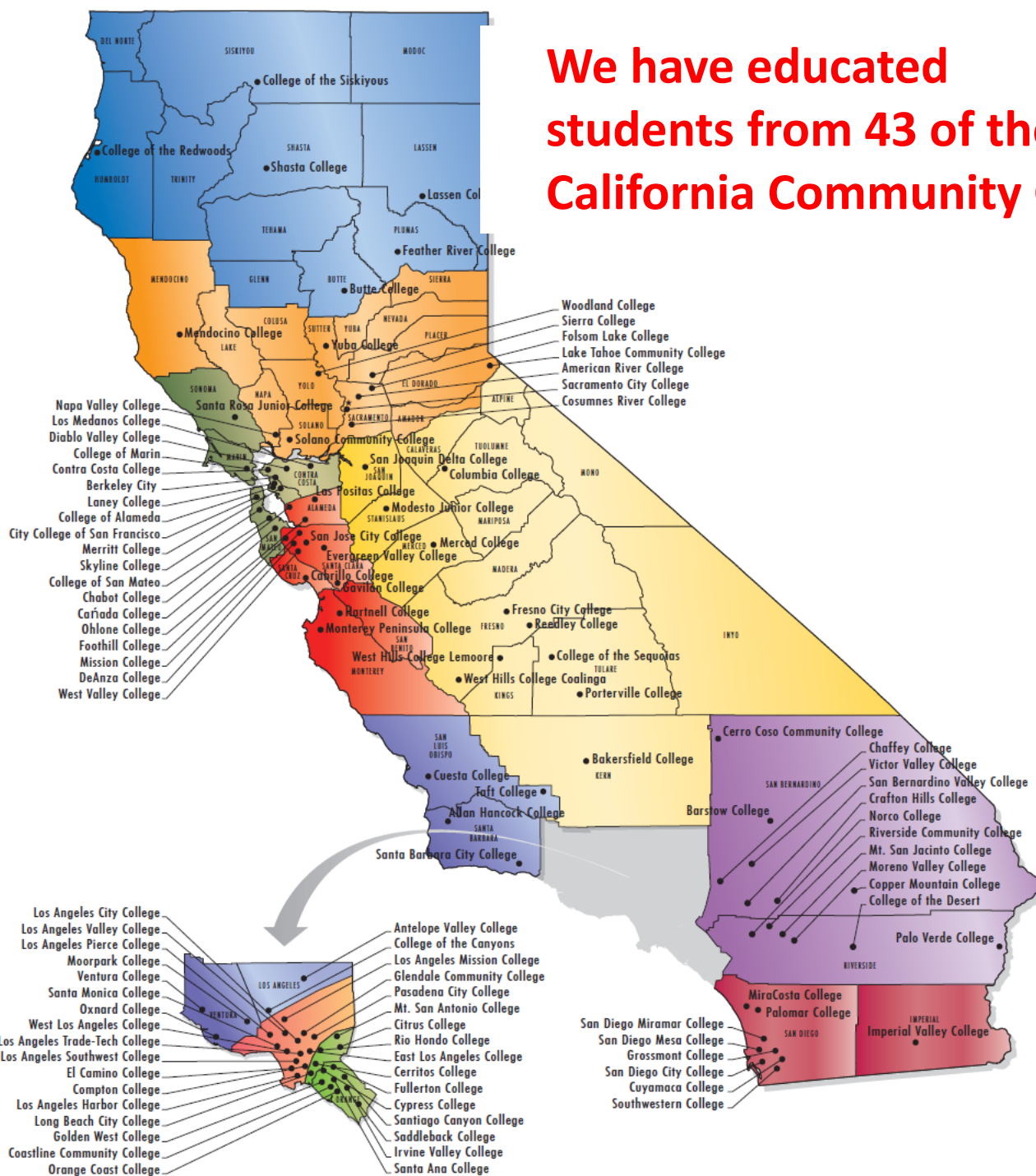
California transfer rate: 40%
Nationwide transfer rate: 67%
TTE transfer rate: 93% (64) of eligible students

- 88% (56) enrolled at a UC campus
 - 61% (39) enrolled at Berkeley
- 93% (78) from underrepresented groups

EEC 1157089
EEC 1461157

American Association of Community Colleges (AACC). (2012a, April)., Reclaiming the American Dream: A report from the 21st-Century Commission on the Future of Community Colleges., Washington, DC: Author. <http://datamart.cccco.edu>

We have educated students from 43 of the 114 California Community Colleges



10/30/2018

A Science & Technology